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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	626	source.clm. and drain.clm. and trench.clm. and (trench adj isolation).clm. and gate.clm.	USPAT	OR	ON	2006/06/20 10:51
L7	572	source.clm. and drain.clm. and trench.clm. and (trench adj isolation).clm. and gate.clm. and substrate.clm.	USPAT	OR	ON	2006/06/20 10:51
L8	27	source.clm. and drain.clm. and trench.clm. and (trench adj isolation).clm. and gate.clm. and substrate.clm. and (deep adj trench).clm.	USPAT	OR	ON	2006/06/20 10:52
L9	2144	257/501,506,510.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 10:59
L10	1270	257/506.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 11:00
L11	938	257/510.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 11:01
S1	2	("6501149").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 13:48
S2	791	"257".clas. and Idmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:03
S3	791	"257".clas. and Idmos and ap<"20040409"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:03

S4	748	"257".clas. and Idmos and @ad<"20040409"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2005/07/29 14:03
S5	254	"257".clas. and Idmos and @ad<"20040409" and trench	IBM_TDB US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:05
S6	53	"257".clas. and ldmos and @ad<"20040409" and trench and leakage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:51
S7	65	"257".clas. and Idmos and @ad<"20040409" and (trench or STI or LOCOS) and leakage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/07/29 15:36
S8	492	(257/499).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 13:48
S9	120	257/499.ccls. and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 13:54
S10	114	257/499.ccls. and trench and @ad<"20040409"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:46
S11	609	257/510.ccls. and trench and @ad<"20040409"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 10:59

S12	486	257/510.ccls. and trench and @ad<"20040409" and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 09:01
S13	218	257/510.ccls. and trench and @ad<"20040409" and transistor and leakage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:47
S14	63	257/510.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:27
S15	9	257/511.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:32
S16	1	257/512.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:33
S17	24	257/513.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:39
S18	11	257/514.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:46
S19	7	257/515.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:46

S20	3	257/547.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:49
S21	17	257/335.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 15:59
S22	158	438/424.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 12:45
S23	256	trench and @ad<"20040409" and (("corner vt") or ("corner transistor") or ("gate edge drain leakage") or ("corner leakage") or ("edge conduction") or ("sidewall leakage") or ("side-wall leakage") or ("edge leakage"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 14:01
S24	253	257/408.ccls. and trench and @ad<"20040409"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 14:01
S25	241	257/408.ccls. and trench and @ad<"20040409" and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 14:02
S26	48	257/506.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 16:27
S27	3	257/213.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 13:25

S28	89	trench and @ad<"20040409" and (transistor with leakage) and (strained or SMOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:31
S29	97	trench and @ad<"20040409" and (transistor with leakage) and ("body contact")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 12:00
S30	2	("20020038901").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/15 10:00
S31	345	(@ad<"20040409" or @rlad<"20040409") and trench and Idmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 08:22
S34	2	"20020038901"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/04 14:39
S35	26081	(@ad<"20040409" or @rlad<"20040409") and trench and gate and drain and source	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/04 18:11
S36	18027	(@ad<"20040409" or @rlad<"20040409") and trench and gate and drain and source and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/04 18:11
S37	4132	(@ad<"20040409" or @rlad<"20040409") and trench and gate and drain and source and isolation and "leakage current"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/04 18:12

S38	4053	(@ad<"20040409" or @rlad<"20040409") and trench and gate and drain and source and isolation and "leakage current"	US-PGPUB; USPAT	OR	ON	2006/02/04 18:44
S39	292	(@ad<"20040409" or @rlad<"20040409") and trench and gate and drain and source and isolation and (deep adj trench adj isolation)	US-PGPUB; USPAT	OR	ON	2006/02/06 12:14
S40	1	"20010035774"	US-PGPUB; USPAT	OR	OFF	2006/02/06 08:06
S41	23	(@ad<"20040409" or @rlad<"20040409") and trench and gate and drain and source and isolation and (deep adj trench adj isolation) and (dmos or Idmos)	US-PGPUB; USPAT	OR	ON	2006/02/06 12:14
S42	9	"6501149"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 08:22
S43	539	257/510.ccls. and trench and (@ad<"20040409" or @rlad<"20040409") and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 12:25
S44	996	trench and (@ad<"20040409" or @rlad<"20040409") and ("body contact")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 12:01
S45	6	"6501149"	USPAT	OR	OFF	2006/02/08 08:20
S46	0	"20030155592"	USPAT	OR	OFF	2006/02/08 08:49
S47	1	"20030155592"	US-PGPUB; USPAT	OR	OFF	2006/02/08 08:49
S48	64	257/511.ccls. and trench and (@ad<"20040409" or @rlad<"20040409") and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 12:25

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S49	21	257/512.ccls. and trench and (@ad<"20040409" or @rlad<"20040409") and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	ON	2006/02/08 12:26
			DERWENT; IBM_TDB			

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